

MAR 14 2005

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Multiple sheets used when necessary)

SHEET 1 OF 3

Application No.	10/800,417
Filing Date	March 11, 2004
First Named Inventor	Chantal J. Arena
Art Unit	2812
Examiner	Unknown
Attorney Docket No.	ASMEX.446A

## U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
S.W.S.	1	6,646,073	04/2003 11/2003	Kondo - Farrer et al.	
S.W.S.	2	6,709,901	03/2004	Yamazaki, et al.	
S.W.S.	3	2002/0173130 AI	11/2002	Pomerede, et al.	
S.W.S.	4	3,602,778	08/31/71	Ura, et al	
S.W.S.	5	3,720,877	03/13/73	Zarowin	
S.W.S.	6	3,729,645	04/24/73	Redington	
S.W.S.	7	3,737,739	06/05/73	Blakeslee, et al.	
S.W.S.	8	3,984,718	10/05/76	Fein, et al.	
S.W.S.	9	3,984,857	10/05/76	Mason	
S.W.S.	10	3,985,590	10/12/76	Mason	
S.W.S.	11	4,461,820	07/24/84	Shirai, et al.	
S.W.S.	12	4,656,013	04/07/87	Hiai, et al.	
S.W.S.	13	4,699,892	10/13/87	Suzuki	
S.W.S.	14	4,786,574	11/22/88	Shirai, et al.	
S.W.S.	15	4,803,186	02/07/89	Chen, et al.	
S.W.S.	16	4,857,270	08/15/89	Maruya, et al.	
S.W.S.	17	4,868,014	09/19/89	Kanai, et al.	
S.W.S.	18	4,983,274	01/08/91	Chen, et al.	
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S.W.S.	21	5,281,274	01/25/94	Yoder	
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S.W.S.	28	5,646,073	07/08/97	Grider, et al.	
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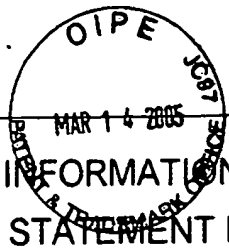
Examiner Signature

Stephen W. Smoot

Date Considered October 14, 2005

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S.W.S.	30	5,818,100	10/06/98	Grider, et al.	
S.W.S.	31	6,242,080 B1	06/05/01	Kondo	
S.W.S.	32	6,451,641 B1	09/17/02	Halliyal, et al.	
S.W.S.	33	6,515,219 B2	02/04/03	Kondo	
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S.W.S.	36	2003/0157787 A1	08/21/03	Murthy et al.	
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S.W.S.	39	2003/0230233 A1	12/18/03	Fitzgerald et al.	

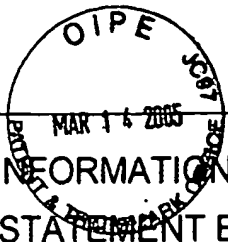
FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T <sup>1</sup>
S.W.S.	40	JP 62017004	01/26/87	Japan		

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
S.W.S.	41	TAKAGI ET AL., "Device structure and electrical characteristics of strained-Si-on-insulator (strained-SOI) MOSFETs", Materials Science and Engineering B89 (2002), pp. 426-434	
S.W.S.	42	LIM ET AL., "Dry thermal oxidation of a graded SiGe layer", Applied Physics Letters, Vol. 79, No. 22, November 26, 2001, pp. 3606-3608	
S.W.S.	43	SUGIYAMA ET AL., "Fabrication of SiGe on Insulator Structure using Ge Condensation Technique", Third International Conference on SiGe (C) Epitaxy and Heterostructures (ICS13), Santa Fe, NM, March 9-12, 2003, pp. 153-154	
S.W.S.	44	MIZUNO ET AL., "Advanced SOI p-MOSFETs with Strained-Si Channel on SiGe-on-Insulator Substrate Fabricated by SIMOX Technology", IEEE Transactions on Electron Devices, Vol. 48, No. 8, August 2001, pp. 1612-1618	
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## NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>1</sup>
S.W.S.	47	TSUTOMU TEZUKA, "Strained Si- and SiGe-MOSFETs on SiGe-on-insulator (SGOI) substrates", 2002 Japan Epitaxial Technology Symposium, "Advanced Substrate Engineering and Device Technology", February 27, 2002	
S.W.S.	48	TEZUKA ET AL., "Fabrication of strained Si on an ultrathin SiGe-on-insulator virtual substrate with a high-Ge fraction", Applied Physics Letters, Vol 79, No. 12, September 17, 2001, pp. 1798-1800	
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S.W.S.	56	ISHIKAWA, Y. ET AL., "Strain-induced band gap shrinkage in Ge grown on Si substrate", Applied Physics Letters, Volume 82, Number 12, March 31, 2003, pp. 2044-2046.	
S.W.S.	57	LEE ET AL., "Growth of strained Si and strained Ge heterostructures on relaxed Si <sub>1-x</sub> Ge <sub>x</sub> by ultrahigh vacuum chemical vapor deposition", J. Vac. Sci. Technol. B 22(1) (Jan/Feb 2004), pp. 158-164.	
S.W.S.	58	LI, Q. ET AL., "Selective growth of Ge on Si(100) through vias of SiO <sub>2</sub> nanotemplate using solid source molecular beam epitaxy", Applied Physics Letters, Volume 83, Number 24, December 15, 2003, pp. 5032-5034.	
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